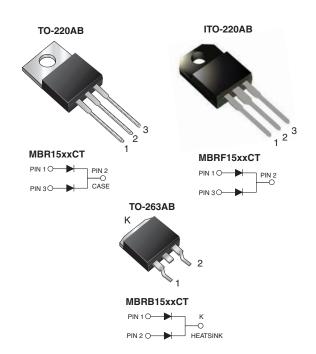


### MBR(F,B)1535CT thru MBR(F,B)1560CT

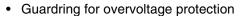
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# **Dual Common-Cathode Schottky Rectifier**



MAJOR RATINGS AND CHARACTERISTICS					
I <sub>F(AV)</sub>	7.5 A x 2				
V <sub>RRM</sub>	35 V to 60 V				
I <sub>FSM</sub>	150 A				
V <sub>F</sub>	0.57 V, 0.65 V				
T <sub>j</sub> max	150 °C				

#### **FEATURES**





- Lower power losses, high efficiency
- · Low forward voltage drop
- · High forward surge capability
- · High frequency operation
- Meets MSL level 1, per J-STD-020C, LF max peak of 245 °C (for TO-263AB package)
- Solder Dip 260 °C, 40 seconds (for TO-220AB & ITO-220AB package)
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

#### **TYPICAL APPLICATIONS**

For use in high frequency rectifier of switching mode power supplies, free-wheeling diodes, dc-to-dc converters or polarity protection application.

#### **MECHANICAL DATA**

Case: TO-220AB, ITO-220AB, TO-263AB Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per

J-STD-002B and JESD22-B102D

E3 suffix for commercial grade, HE3 suffix for high

reliability grade (AEC Q101 qualified)

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

MAXIMUM RATINGS (T <sub>C</sub> = 25 °C unless otherwise noted)							
PARAMETER	SYMBOL	MBR1535CT	MBR1545CT	MBR1550CT	MBR1560CT	UNIT	
Maximum repetitive peak reverse voltage	$V_{RRM}$	35	45	50	60	٧	
Working peak reverse voltage	$V_{RWM}$	35	45	50	60	٧	
Maximum DC blocking voltage	$V_{DC}$	35	45	50	60	٧	
Maximum average forward rectified Total device current at $T_C = 105$ °C per diode	I <sub>F(AV)</sub>	15 7.5			А		
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I <sub>FSM</sub>	и 150			Α		
Peak repetitive reverse surge current per diode at $t_p = 2.0 \ \mu s, \ 1 \ kHz$	I <sub>RRM</sub>	1.0 0.5		.5	Α		
Voltage rate of change (rated V <sub>R</sub> )	dv/dt	10000			V/µs		
Operating junction temperature range	TJ	- 65 to + 150		°C			

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MAXIMUM RATINGS (T <sub>C</sub> = 25 °C unless otherwise noted)							
PARAMETER	SYMBOL MBR1535CT MBR1545CT MBR1550CT MBR1560CT U					UNIT	
Storage temperature range	T <sub>STG</sub>	- 65 to + 175			°C		
Isolation voltage (ITO-220AB only) From terminal to heatsink t = 1 minute	V <sub>AC</sub>	1500			٧		

<b>ELECTRICAL CHARACTERISTICS</b> (T <sub>C</sub> = 25 °C unless otherwise noted)								
PARAMETER	TEST CONDITIONS	SYMBOL	MBR1535CT	MBR1545CT	MBR1550CT	MBR1560CT	UNIT	
Maximum instantaneous forward voltage per diode <sup>(1)</sup>	at $I_F = 7.5$ A, $T_C = 25$ °C at $I_F = 7.5$ A, $T_C = 125$ °C at $I_F = 15$ A, $T_C = 25$ °C at $I_F = 15$ A, $T_C = 125$ °C	V <sub>F</sub>	- 0.57 0.84 0.72		-	75 65 -	٧	
Maximum instantaneous reverse current at rated DC blocking voltage per diode (1)	T <sub>C</sub> = 25 °C T <sub>C</sub> =125 °C	I <sub>R</sub>	0.1 15		-	0.0	mA	

#### Note:

(1) Pulse test: 300  $\mu$ s pulse width, 1 % duty cycle

THERMAL CHARACTERISTICS (T <sub>C</sub> = 25 °C unless otherwise noted)							
PARAMETER SYMBOL MBR MBRF MBRB					UNIT		
Maximum thermal resistance per diode	$R_{ heta JA} \ R_{ heta JC}$	60 3.0	- 5.0	60 3.0	°C/W		

ORDERING INFORMATION							
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE		
TO-220AB	MBR1545CT-E3/45	1.85	45	50/Tube	Tube		
ITO-220AB	MBRF1545CT-E3/45	1.99	45	50/Tube	Tube		
TO-263AB	MBRB1545CT-E3/45	1.35	45	50/Tube	Tube		
TO-263AB	MBRB1545CT-E3/81	1.35	81	800/Reel	Tape Reel		

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#### **RATINGS AND CHARACTERISTICS CURVES**

 $(T_A = 25 \, ^{\circ}C \text{ unless otherwise noted})$ 

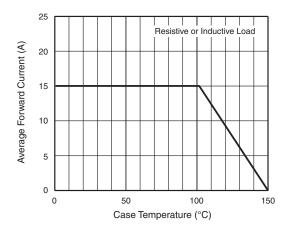


Figure 1. Forward Current Derating Curve

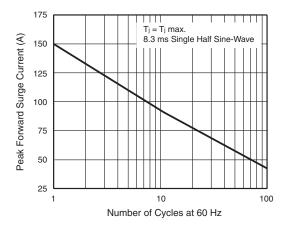


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current Per Diode

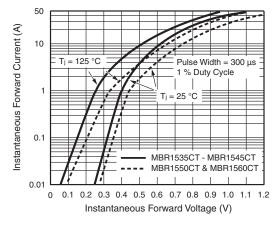


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

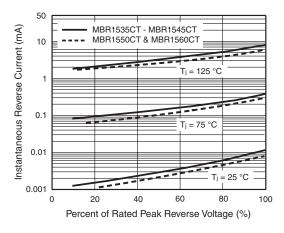


Figure 4. Typical Reverse Characteristics Per Diode

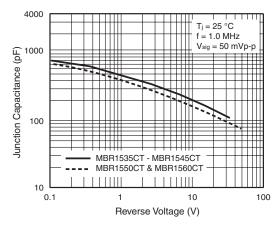


Figure 5. Typical Junction Capacitance Per Diode

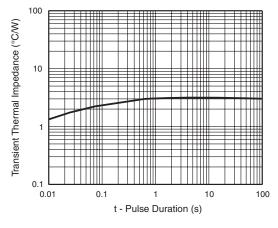


Figure 6. Typical Transient Thermal Impedance Per Diode

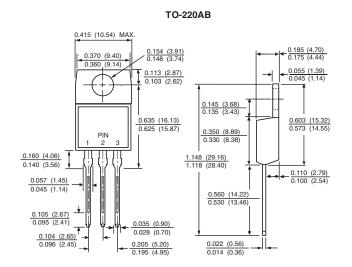
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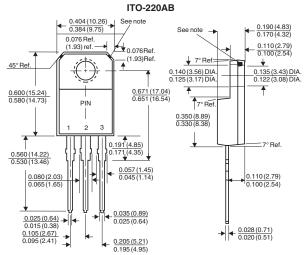
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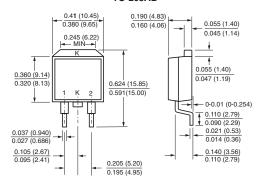
#### **PACKAGE OUTLINE DIMENSIONS** in inches (millimeters)



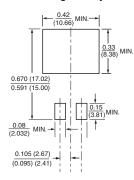


Note: Copper exposure is allowable for 0.005 (0.13) Max. from the body

#### TO-263AB



#### **Mounting Pad Layout**



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### **Legal Disclaimer Notice**



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